

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property
Organization
International Bureau

(43) International Publication Date
25 August 2022 (25.08.2022)



(10) International Publication Number
WO 2022/177504 A1

(51) International Patent Classification:
H01L 29/778 (2006.01) *H01L 29/49* (2006.01)
H01L 29/45 (2006.01)

(21) International Application Number:
PCT/SG2022/050005

(22) International Filing Date:
04 January 2022 (04.01.2022)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
10202101764X 22 February 2021 (22.02.2021) SG

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(81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BN, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CZ, DE, DJ, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IR, IS, IT, JO, JP, KE, KG, KH, KN, KP, KR, KW, KZ, LA, LC, LK, LR, LS, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PA, PE, PG, PH, PL, PT, QA, RO, RS, RU, RW, SA, SC, SD, SE, SG, SK, SL, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, WS, ZA, ZM, ZW.

(84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LR, LS, MW, MZ, NA, RW, SD, SL, ST, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, RU, TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV,

(54) Title: SEMICONDUCTOR APPARATUS AND METHOD FOR FABRICATING THEREOF

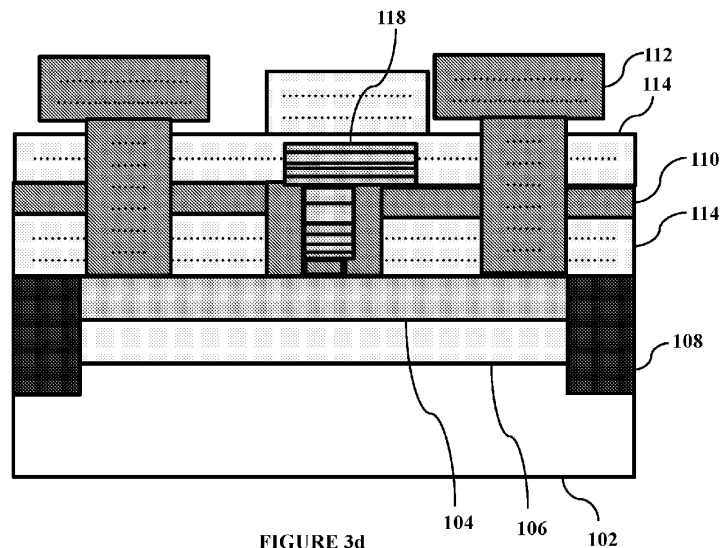


FIGURE 3d

(57) Abstract: The present invention relates to a semiconductor apparatus (3000). A semiconductor apparatus (3000) comprising a heavy doped poly Si film (118) deposited on a gate insulation film (110). A dielectric film (114) is deposited on the gate insulation film (110) and the heavy doped poly Si film (118) followed by an ohmic contact opening to etch away the dielectric film (114) and the gate insulation film (110) to expose an ohmic contact area. At least one ohmic contact metal (112) is deposited and patterned on a portion of the AlGaIn barrier (104). The at least one ohmic contact metal (112) is deposited and patterned on at least one of a portion of the dielectric film (114) and a portion of the gate insulation film (110).

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MC, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM,
TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW,
KM, ML, MR, NE, SN, TD, TG).

Published:

— *with international search report (Art. 21(3))*